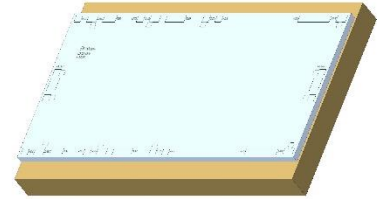


### Product Description

The Nxbeam NPA2001-TB-501 is a Ka-band high power amplifier MMIC fabricated in 0.2um GaN HEMT on SiC mounted on a high thermal conductive heat spreader (tab). The MMIC operates from 26.5 to 29.5 GHz and provides 35 W saturated output power, 31% PAE, and 25 dB of linear gain. The NPA2001-TB-501 comes in die-on-tab form with RF input and output matched to 50 Ω with DC blocking capacitors for easy system integration. The HEMT devices are fully passivated for reliable operation. Bond pad and backside metallization are Au-based for compatibility with eutectic die attachment methods.



### Applications

- 5G mmWave (n257)
- Ka-band Satellite Communications
- Point-to-Point/Multipoint Digital Radios

### Key Features

- Frequency: 26.5 – 29.5 GHz
- Linear Gain: 25 dB
- Psat: 35 W
- PAE: 31%

### Electrical Specifications

Test Condition:  $V_d = 24\text{ V}$ ,  $I_{dq} = 2.18\text{ A}$ , CW Performance in Fixture, Typical Performance at 25°C

| Parameter                          |        | Min  | Typical | Max  | Unit |
|------------------------------------|--------|------|---------|------|------|
| Frequency                          |        | 26.5 |         | 29.5 | GHz  |
| Gain (Small Signal)                | 27 GHz |      | 25      |      | dB   |
|                                    | 28 GHz |      | 25      |      |      |
|                                    | 29 GHz |      | 25      |      |      |
| Output Power (at Psat, Pin=26 dBm) | 27 GHz |      | 45.6    |      | dBm  |
|                                    | 28 GHz |      | 45.4    |      |      |
|                                    | 29 GHz |      | 45.4    |      |      |
| PAE (at Psat, Pin=26 dBm)          | 27 GHz |      | 32.5    |      | %    |
|                                    | 28 GHz |      | 31.4    |      |      |
|                                    | 29 GHz |      | 31.0    |      |      |
| Power Gain (at Psat, Pin=26 dBm)   | 27 GHz |      | 20.5    |      | dB   |
|                                    | 28 GHz |      | 20.3    |      |      |
|                                    | 29 GHz |      | 19.7    |      |      |
| Input Return Loss                  | 27 GHz |      | 20      |      | dB   |
|                                    | 28 GHz |      | 12      |      |      |
|                                    | 29 GHz |      | 15      |      |      |
| Output Return Loss                 | 27 GHz |      | 14      |      | dB   |
|                                    | 28 GHz |      | 14      |      |      |
|                                    | 29 GHz |      | 13      |      |      |

### Maximum Quiescent Bias

| Parameter                     | Max  | Unit |
|-------------------------------|------|------|
| Drain Voltage (Vd1, Vd2, Vd3) | 28   | V    |
| Drain Current (Id1)           | 264  | mA   |
| Drain Current (Id2)           | 640  | mA   |
| Drain Current (Id3)           | 2560 | mA   |

Maximum quiescent bias represents the operational bias used during reliability life testing. Biasing the part at or below this bias ensures reliability will be bound by the published reliability results.

### Absolute Maximum Ratings (Temp. = 25°C)

| Parameter                     | Min | Max  | Unit |
|-------------------------------|-----|------|------|
| Drain Voltage (Vd1, Vd2, Vd3) |     | 28   | V    |
| Drain Current (Id1)           |     | 660  | mA   |
| Drain Current (Id2)           |     | 1600 | mA   |
| Drain Current (Id3)           |     | 6400 | mA   |
| Gate Voltage (Vg1, Vg2, Vg3)  | -8  | 0    | V    |

### Recommended Quiescent Operating Condition

| Parameter                         | Value      | Unit |
|-----------------------------------|------------|------|
| Drain Voltage (Vd)                | 20 - 28    | V    |
| Drain Current (Id1)               | up to 264  | mA   |
| Drain Current (Id2)               | up to 640  | mA   |
| Drain Current (Id3)               | up to 2560 | mA   |
| Gate Voltage (Vg) (Typical Range) | -4         | V    |

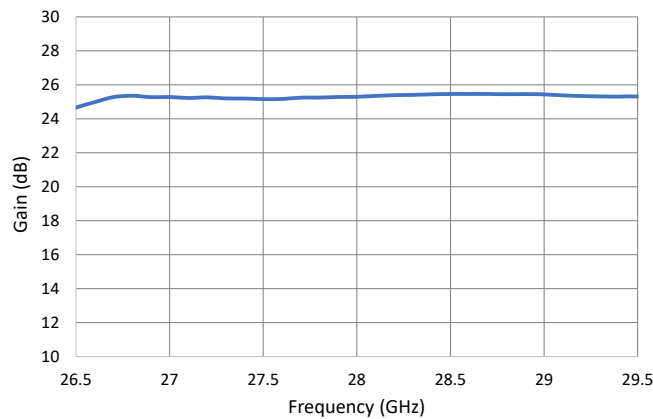
Absolute maximum ratings represent the maximum current under power saturation conditions.

Gate voltage will vary based on desired current per stage

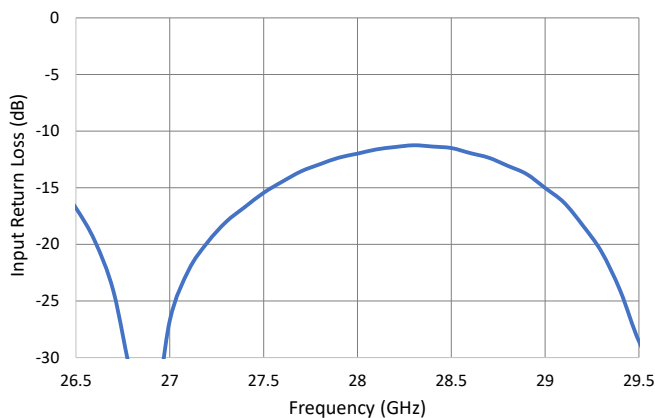
### Small Signal Performance

Test Condition: Vd = 24 V, Idq = 2.18 A, (CW Performance in Fixture, Typical Performance at 25°C)

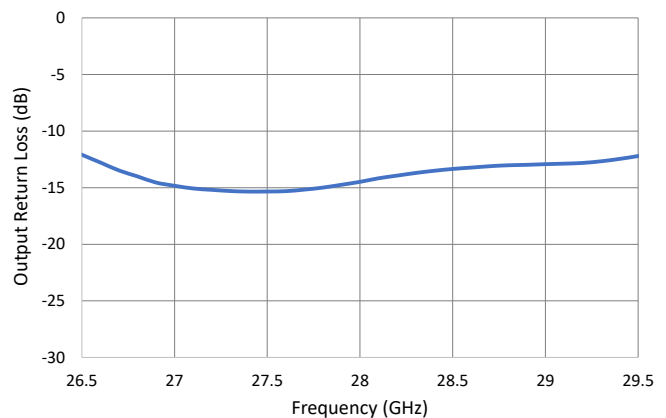
Gain vs. Frequency



Input Return Loss vs. Frequency



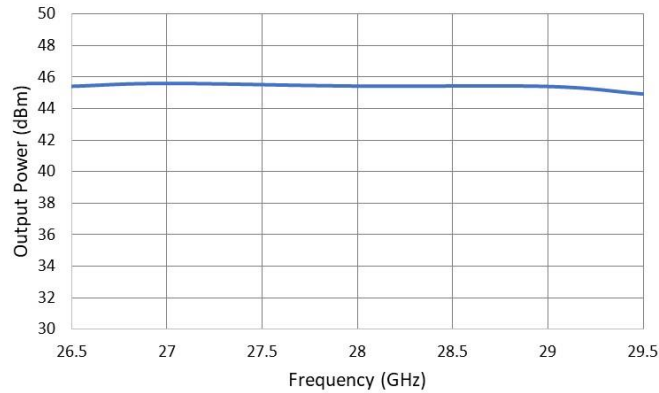
Output Return Loss vs. Frequency



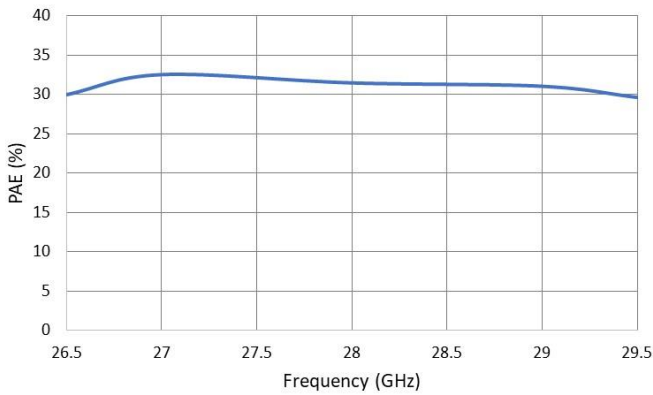
### Large Signal Performance

Test Condition:  $V_d = 24\text{ V}$ ,  $I_{dq} = 2.18\text{ A}$ ,  $P_{in} = 26\text{ dBm}$  ( $P_{sat}$ )  
 (CW Performance in Fixture, Typical Performance at 25°C)

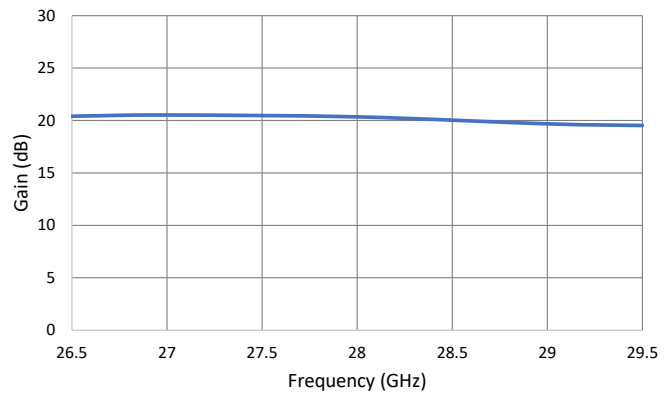
Output Power vs. Frequency (at 26 dBm Pin)



PAE vs. Frequency (at 26 dBm Pin)



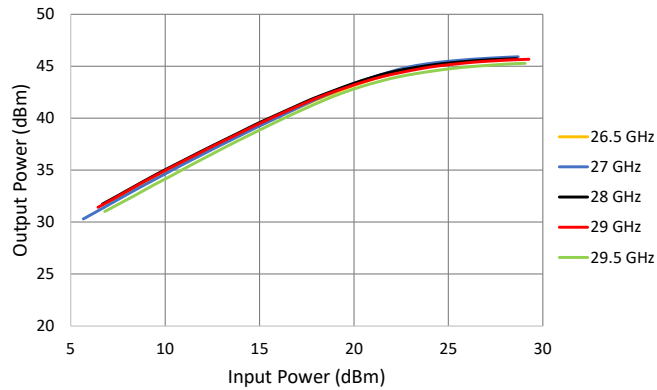
Gain vs. Frequency (at 26 dBm Pin)



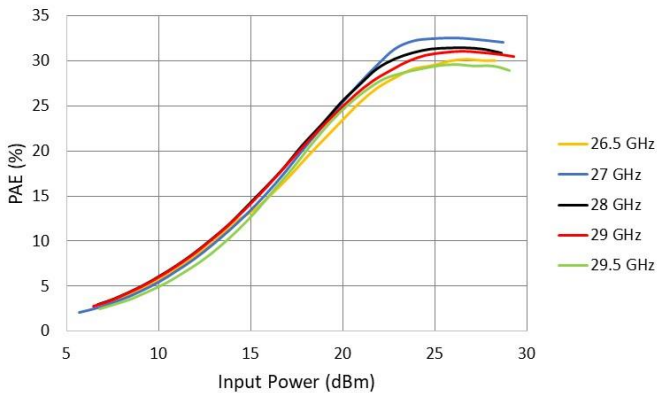
### Large Signal Performance

Test Condition:  $V_d = 24\text{ V}$ ,  $I_{dq} = 2.18\text{ A}$ ,  
 (CW Performance in Fixture, Typical Performance at 25°C)

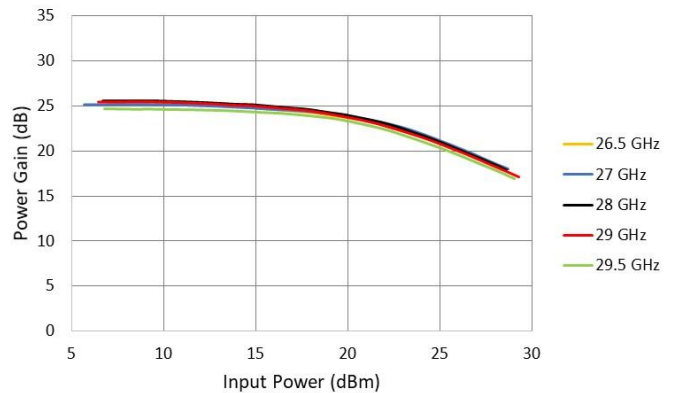
Output Power vs. Input Power vs. Frequency



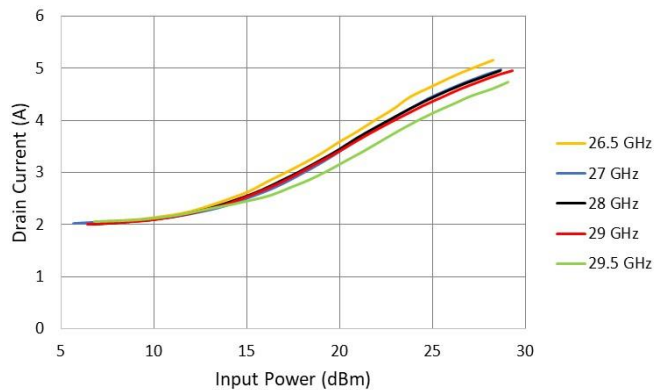
PAE vs. Input Power vs. Frequency



Power Gain vs. Input Power vs. Frequency



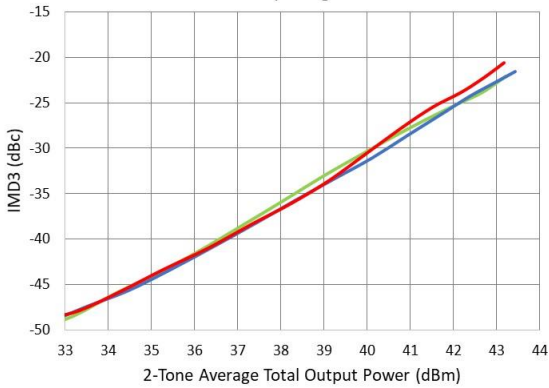
Drain Current vs. Input Power vs. Frequency



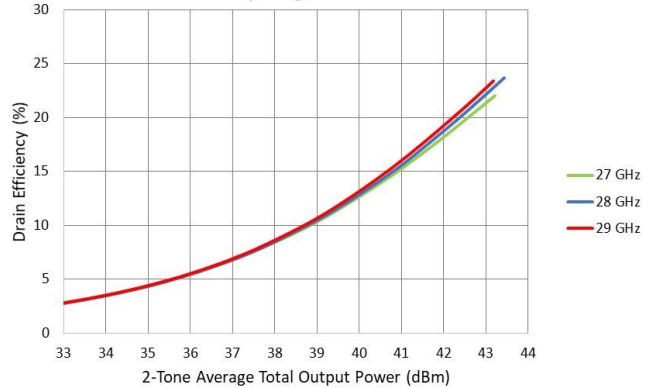
### 2-Tone Linearity Performance

CW Performance in Fixture, Typical Performance at 25°C,  
Bias as Listed in Figure

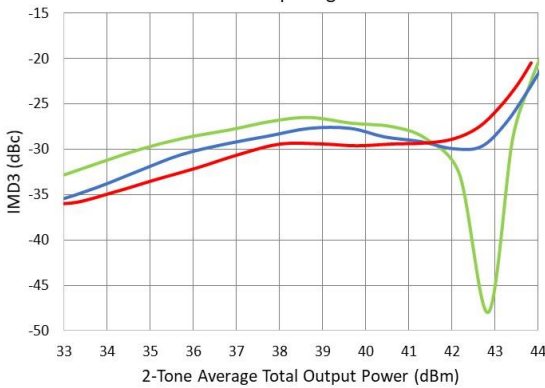
IMD3 vs. 2-Tone Output Power vs. Frequency  
Vd = 26 V, Idq= 2.75 A (Vg1=Vg2=Vg3)  
Tone Spacing: 10MHz



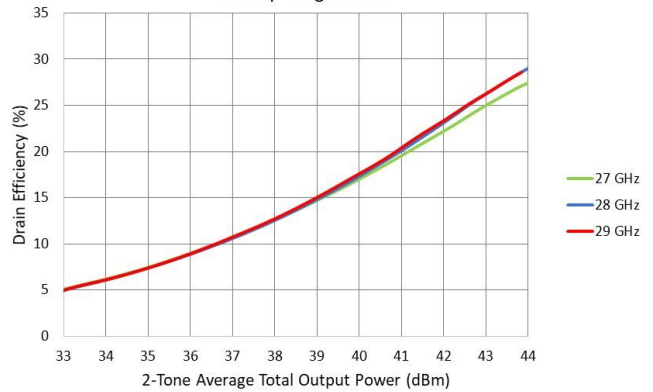
Drain Efficiency vs. 2-Tone Output Power vs. Frequency  
Vd = 26 V, Idq= 2.75 A (Vg1=Vg2=Vg3)  
Tone Spacing: 10MHz



IMD3 vs. 2-Tone Output Power vs. Frequency  
Vd = 26 V, Idq= 1.3 A (Id1= 260mA, Id2=80mA, Id3=930mA)  
Tone Spacing: 10MHz



Drain Efficiency vs. 2-Tone Output Power vs. Frequency  
Vd = 26 V, Idq= v1.3 A (Id1= 260mA, Id2=80mA, Id3=930mA)  
Tone Spacing: 10MHz



### Thermal Information

RF = Off

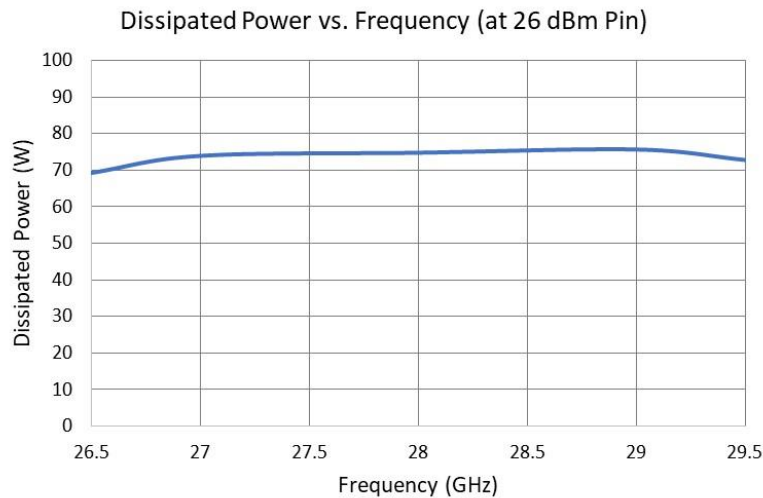
| Parameter                              | Condition  | Value | Unit |
|--|--|-------|------|
| Thermal Resistance ( $R_{\theta JC}$ ) | RF=OFF   | 1.24  | °C/W |
| Junction Temperature ( $T_j$ )         | $T_{backside}=85\text{ °C}$ , $V_d=24\text{ V}$ , $I_{dq}=2.18\text{ A}$ , $P_{dis}=52.3\text{ W}$ | 149.9 | °C   |

RF = On, Peak Junction Temperature at Pin = 26 dBm ( $P_{sat}$ ),  
CW Performance in Fixture

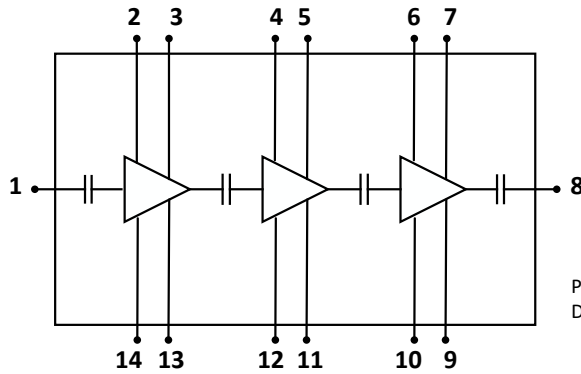
| Parameter                              | Condition   | Value | Unit |
|--|---|-------|------|
| Thermal Resistance ( $R_{\theta JC}$ ) | $P_{in}=26\text{ dBm}$ , Freq.=29 GHz   | 1.29  | °C/W |
| Junction Temperature ( $T_j$ )         | $T_{backside}=85\text{ °C}$ , $V_d=24\text{ V}$ , $I_d=4.59\text{ A}$ , $P_{dis}=75.7\text{ W}$ | 182.7 | °C   |

Note 1: Thermal resistance determined to the back of the tab.

Note 2: Mean time to failure per junction temperature information can be found in the following document:  
[Nxbeam\\_GaN20MMIC\\_Reliability.pdf](#)

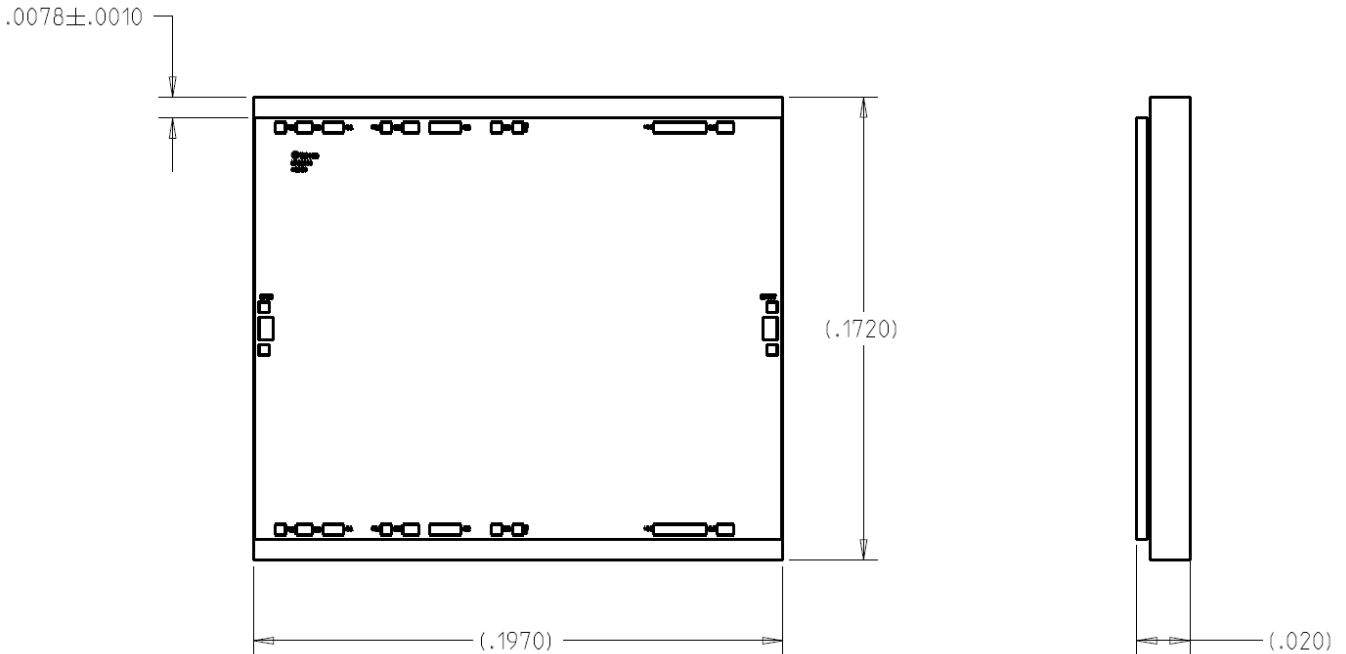


### Circuit Block Diagram



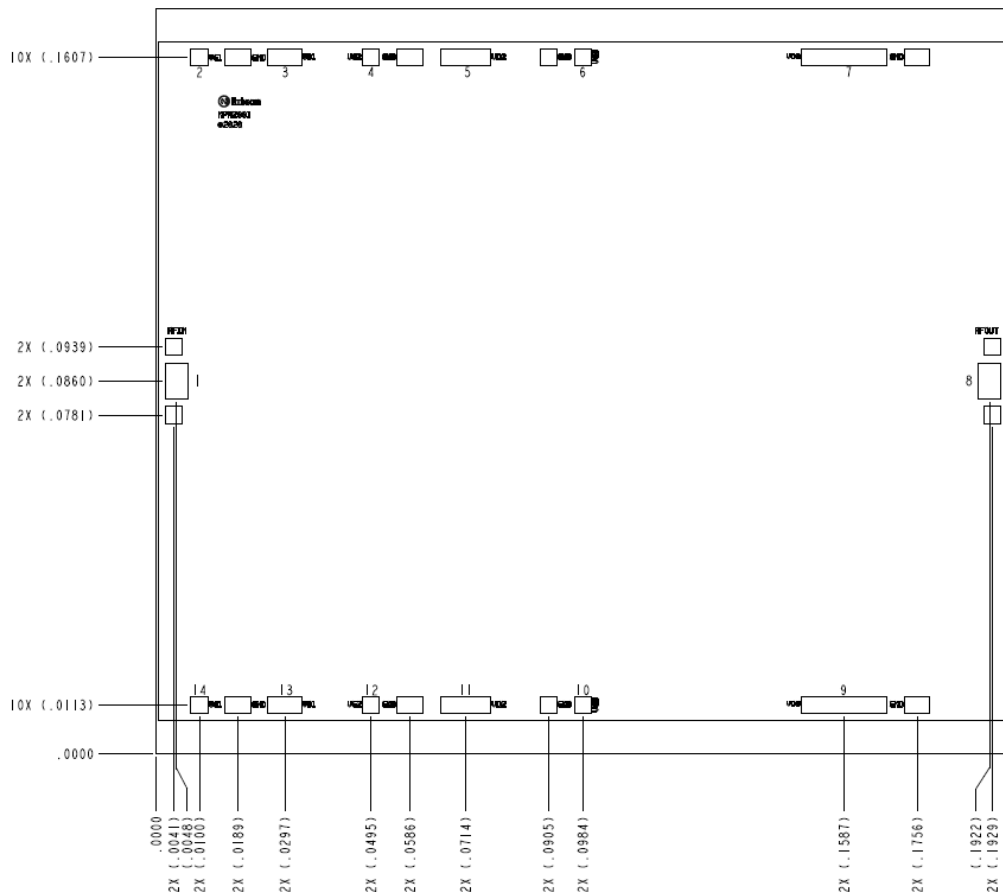
Pin number information detailed under Die Size and Bond Pad Information

### Product Dimensions (all dimensions in inches)



### Die Size and Bond Pad Information

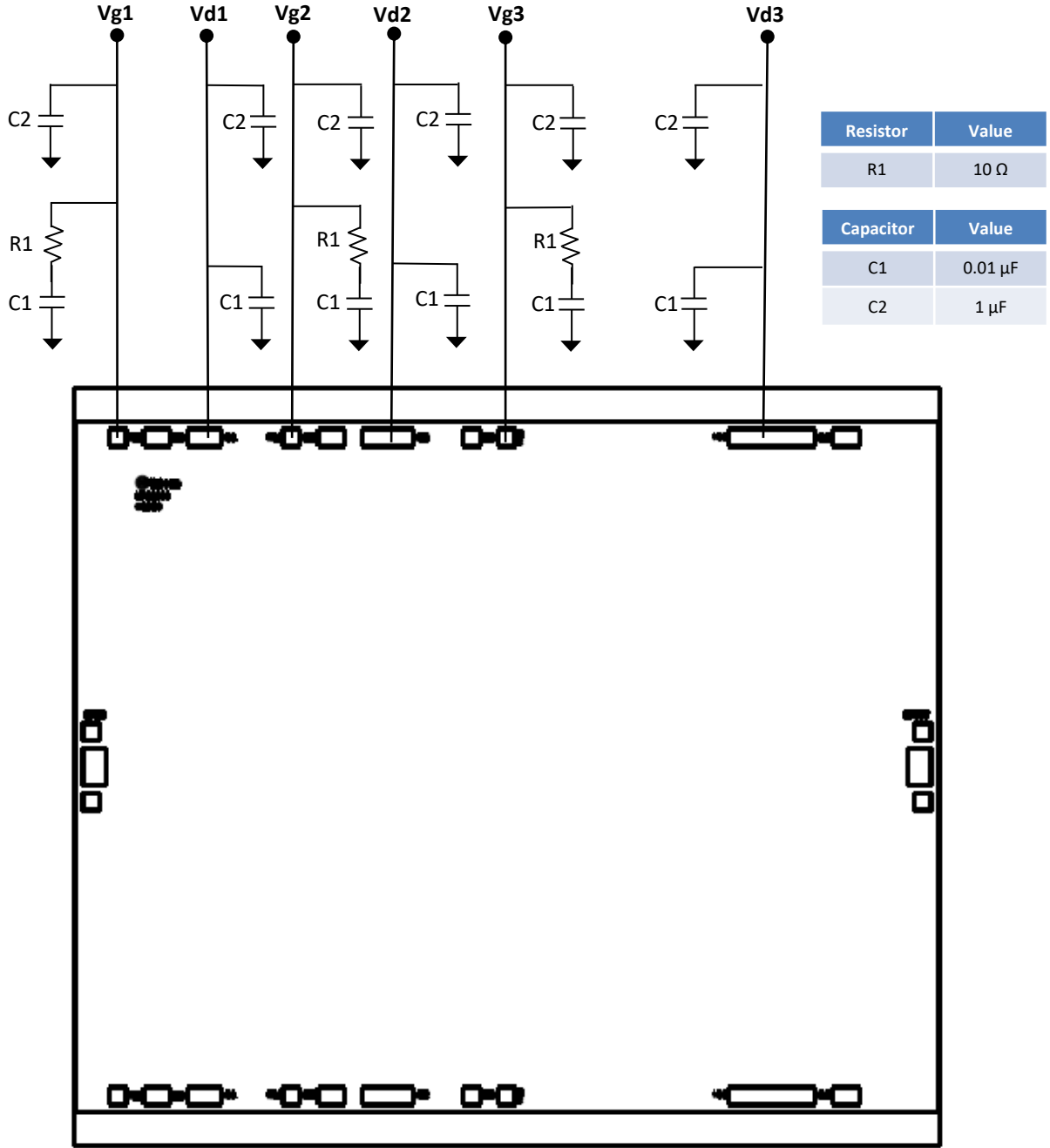
| ID    | FUNCTION                                  | PAD NUMBER | PAD SIZE (MICRONS) |
|-------|---|------------|--------------------|
| RFIN  | RF INPUT                                  | 1          | 134 X 208          |
| RFOUT | RF OUTPUT                                 | 8          | 134 X 208          |
| VG1   | GATE VOLTAGE - STAGE 1 (-8V MIN, 0V MAX)  | 2,14       | 100 X 100          |
| VD1   | DRAIN VOLTAGE - STAGE 1 (0V MIN, 28V MAX) | 3,13       | 196 X 100          |
| VG2   | GATE VOLTAGE - STAGE 2 (-8V MIN, 0V MAX)  | 4,12       | 100 X 100          |
| VD2   | DRAIN VOLTAGE - STAGE 2 (0V MIN, 28V MAX) | 5,11       | 296 X 100          |
| VG3   | GATE VOLTAGE - STAGE 3 (-8V MIN, 0V MAX)  | 6,10       | 96 X 100           |
| VD3   | DRAIN VOLTAGE - STAGE 3 (0V MIN, 28V MAX) | 7,9        | 500 X 100          |





### Suggested Off-Chip Components

The following diagram is a suggested bonding arraignment with off-chip components. All drain connections can be tied together to one source. All gate connections can be tied together to one source if desired. The NPA2001-TB-501 should be biased for both sides of the chip.



## Assembly Process

- The heat spreader is gold plated and can be mounted using either a high thermal conductive epoxy or solder attachment.
- Maximum recommended temperature during product attachment is 260 °C for not more than 60 seconds.
- This product contains metal air bridges so caution should be taken when handling to avoid damage.

## Bias Information

### Bias-up Procedure:

- 1.) It is recommended that voltage and current limits are set on the voltage supply's prior to biasing the product.
- 2.) Ensure power supplies are properly grounded to the product test fixture.
- 3.) Apply a negative gate voltage of -7V to Vg1, Vg2, and Vg3 to ensure all devices are pinched off.
- 4.) Gradually increase the drain bias voltage (Vd1, Vd2, Vd3) to the desired bias level but not to exceed the maximum voltage of 28 V.
- 5.) Gradually increase the gate voltages (Vg1, Vg2, Vg3) while monitoring the drain current until the desired drain current in each stage is achieved.
- 6.) Apply RF signal.

### Bias-down Procedure:

- 1.) Turn off RF signal.
- 2.) Gradually decrease Vg1, Vg2, and Vg3 down to -7 V.
- 3.) Gradually decrease the drain voltages (Vd1, Vd2, Vd3) down to 0 V.
- 4.) Gradually increase gate voltages (Vg1, Vg2, Vg3) to 0 V.
- 5.) Turn off supply voltages

## ESD Sensitive Product



## Important Information

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